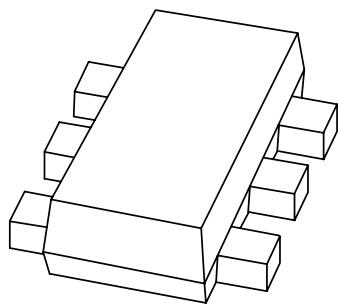


DATA SHEET



PEMB11
PNP resistor-equipped transistors;
 $R1 = 10 \text{ k}\Omega$, $R2 = 10 \text{ k}\Omega$

Preliminary specification

2001 Sep 13

PNP resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

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FEATURES

- 300 mW total power dissipation
- Very small 1.6 mm x 1.2 mm ultra thin package
- Excellent coplanarity due to straight leads
- Replaces two SC-75/SC-89 packaged transistors on same PCB area
- Reduces required PCB area
- Reduced pick and place costs.

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | UNIT |
|-----------|---------------------------|------|------|
| V_{CEO} | collector-emitter voltage | -50 | V |
| I_{CM} | peak collector current | -100 | mA |
| TR1 | PNP | - | - |
| TR2 | PNP | - | - |
| R1 | bias resistor | 10 | kΩ |
| R2 | bias resistor | 10 | kΩ |

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

PINNING

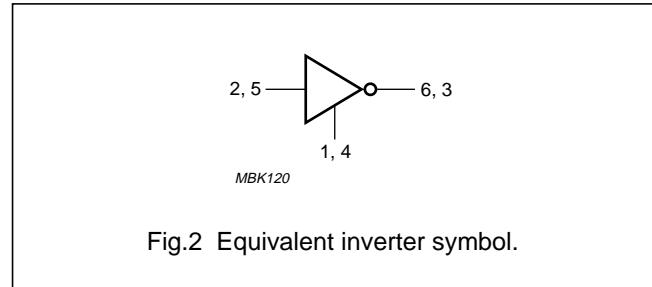
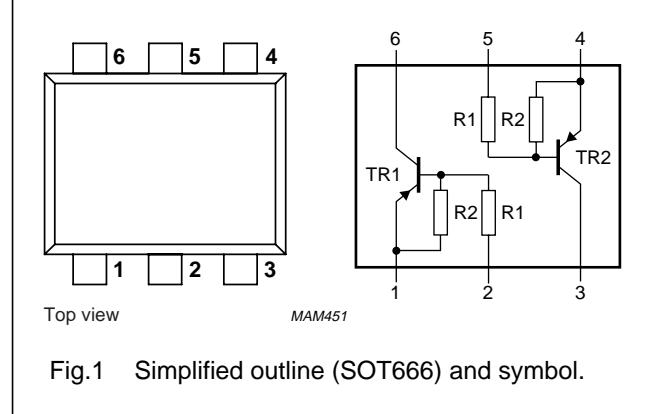
| PIN | DESCRIPTION |
|------|--------------------|
| 1, 4 | emitter TR1; TR2 |
| 2, 5 | base TR1; TR2 |
| 6, 3 | collector TR1; TR2 |

DESCRIPTION

PNP resistor-equipped transistors in a SOT666 plastic package.

MARKING

| TYPE NUMBER | MARKING CODE |
|-------------|--------------|
| PEMB11 | B1 |



PNP resistor-equipped transistors;
 R1 = 10 kΩ, R2 = 10 kΩ

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|--|---------------------------------------|----------------------------------|------|------|------|
| Per transistor unless otherwise specified | | | | | |
| V _{CBO} | collector-base voltage | open emitter | – | –50 | V |
| V _{CEO} | collector-emitter voltage | open base | – | –50 | V |
| V _{EBO} | emitter-base voltage | open collector | – | –10 | V |
| V _I | input voltage positive negative | | – | +10 | V |
| – | | | – | –40 | V |
| I _O | output current (DC) | | – | –100 | mA |
| I _{CM} | peak collector current | | – | –100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C; note 1 | – | 200 | mW |
| T _{stg} | storage temperature | | –65 | +150 | °C |
| T _j | junction temperature | | – | 150 | °C |
| T _{amb} | operating ambient temperature | | –65 | +150 | °C |
| Per device | | | | | |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C; note 1 | – | 300 | mW |

Note

1. Transistor mounted on a FR4 printed-circuit board.

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|---|---------------|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient | notes 1 and 2 | 416 | K/W |

Notes

1. Transistor mounted on an FR4 printed-circuit board.
2. The only recommended soldering method is reflow soldering.

PNP resistor-equipped transistors;
 $R1 = 10 \text{ k}\Omega$, $R2 = 10 \text{ k}\Omega$

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CHARACTERISTICS $T_{\text{amb}} = 25 \text{ }^{\circ}\text{C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--|--------------------------------------|---|------|------|------|------------------|
| Per transistor unless otherwise specified | | | | | | |
| I_{CBO} | collector-base cut-off current | $V_{\text{CB}} = -50 \text{ V}$; $I_{\text{C}} = 0$ | — | — | -100 | nA |
| I_{CEO} | collector-emitter cut-off current | $V_{\text{CE}} = -50 \text{ V}$; $I_{\text{B}} = 0$ | — | — | -1 | μA |
| | | $V_{\text{CE}} = -30 \text{ V}$; $I_{\text{B}} = 0$; $T_j = 150 \text{ }^{\circ}\text{C}$ | — | — | -50 | μA |
| I_{EBO} | emitter-base cut-off current | $V_{\text{EB}} = -5 \text{ V}$; $I_{\text{C}} = 0$ | — | — | -400 | μA |
| h_{FE} | DC current gain | $V_{\text{CE}} = -5 \text{ V}$; $I_{\text{C}} = -5 \text{ mA}$ | 30 | — | — | |
| V_{CEsat} | collector-emitter saturation voltage | $I_{\text{C}} = -10 \text{ mA}$; $I_{\text{B}} = -0.5 \text{ mA}$ | — | — | -150 | mV |
| $V_{i(\text{off})}$ | input off voltage | $V_{\text{CE}} = -5 \text{ V}$; $I_{\text{C}} = -100 \mu\text{A}$ | — | -1.1 | -0.8 | V |
| $V_{i(\text{on})}$ | input on voltage | $V_{\text{CE}} = -0.3 \text{ V}$; $I_{\text{C}} = -10 \text{ mA}$ | -2.5 | -1.8 | — | V |
| $R1$ | input resistor | | 7 | 10 | 13 | $\text{k}\Omega$ |
| $\frac{R2}{R1}$ | resistor ratio | | 0.8 | 1.0 | 1.2 | $\text{k}\Omega$ |
| C_{c} | collector capacitance | $I_{\text{E}} = I_{\text{e}} = 0$; $V_{\text{CB}} = -10 \text{ V}$; $f = 1 \text{ MHz}$ | — | — | 3 | pF |

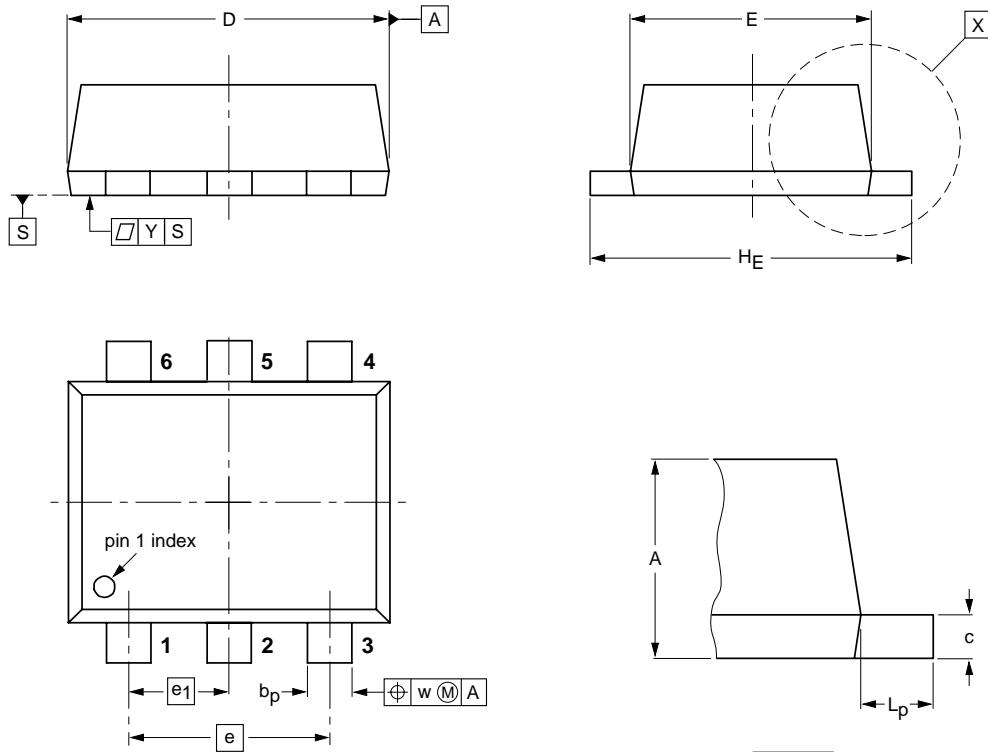
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



DIMENSIONS (mm are the original dimensions)

| UNIT | A | b _p | c | D | E | e | e ₁ | H _E | L _p | w | y |
|------|------------|----------------|--------------|------------|------------|-----|----------------|----------------|----------------|-----|-----|
| mm | 0.6 0.5 | 0.27 0.17 | 0.18 0.08 | 1.7 1.5 | 1.3 1.1 | 1.0 | 0.5 | 1.7 1.5 | 0.3 0.1 | 0.1 | 0.1 |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-------|------|--|---------------------|-----------------------|
| | IEC | JEDEC | EIAJ | | | |
| SOT666 | | | | | | -01-01-04 01-08-27 |

PNP resistor-equipped transistors;
 R1 = 10 kΩ, R2 = 10 kΩ

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|----------------------------------|-------------------------------|--|
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R1 = 10 kΩ, R2 = 10 kΩ

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Contact information

For additional information please visit <http://www.semiconductors.philips.com>. Fax: +31 40 27 24825
For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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